



MMBTA55 / MMBTA56

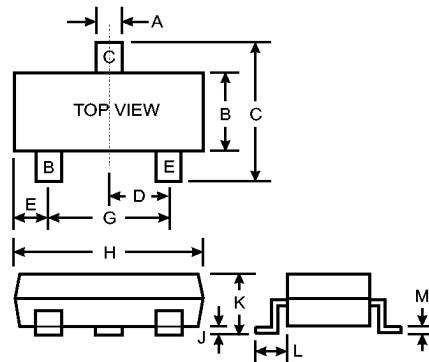
PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA05 / MMBTA06)
- Ideal for Medium Power Amplification and Switching

Mechanical Data

- Case: SOT-23, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- MMBTA55 Marking: K2H, R2H
- MMBTA56 Marking: K2G, R2G
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V_{CB0}	-60	-80	V
Collector-Emitter Voltage	V_{CE0}	-60	-80	V
Emitter-Base Voltage	V_{EB0}	-4.0		V
Collector Current - Continuous (Note 1)	I_C	-500		mA
Power Dissipation (Note 1)	P_d	350		mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	357		K/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150		$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60 -80	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60 -80	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4.0	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	-100	nA	$V_{CB} = -60\text{V}, I_E = 0$ $V_{CB} = -80\text{V}, I_E = 0$
Collector Cutoff Current	I_{CEX}	—	-100	nA	$V_{CE} = -60\text{V}, I_{BO} = 0\text{V}$ $V_{CE} = -80\text{V}, I_{BO} = 0\text{V}$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	100	—	—	$I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25	V	$I_C = -100\text{mA}, I_B = -10\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-1.2	V	$I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f_T	50	—	MHz	$V_{CE} = -1.0\text{V}, I_C = -100\text{mA}, f = 100\text{MHz}$

Note: 1. Valid provided that terminals are kept at ambient temperature.
2. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.